

## -20V P-Channel Power MOSFET



SOP-8

#### Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2 **Key Parameter Performance** 

| Parameter                 |                         | Value | Unit |  |
|---------------------------|-------------------------|-------|------|--|
| $V_{DS}$                  |                         | -20   | V    |  |
| R <sub>DS(on)</sub> (max) | $V_{GS} = -4.5V$        | 60    |      |  |
|                           | V <sub>GS</sub> = -2.7V | 78    | mΩ   |  |
|                           | V <sub>GS</sub> = -2.5V | 85    |      |  |
| $Q_g$                     |                         | 6     | nC   |  |

#### **Features**

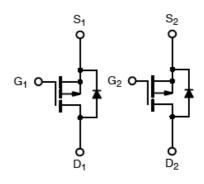
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

#### **Ordering Information**

| Part No.       | Package | Packing           |
|----------------|---------|-------------------|
| TSM9933DCS RLG | SOP-8   | 2.5kps / 13" Reel |

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

#### **Block Diagram**



**Dual P-Channel MOSFET** 

#### **Absolute Maximum Ratings** (T<sub>A</sub>=25°C unless otherwise noted)

| Parameter   |                      | Symbol                            | Limit        | Unit |  |
|---|----------------------|-----------------------------------|--------------|------|--|
| Drain-Source Voltage                                    |                      | $V_{DS}$                          | -20          | V    |  |
| Gate-Source Voltage                                     |                      | $V_{GS}$                          | ±12          | V    |  |
| Continuous Drain Current, V <sub>GS</sub> @ 4.5V.       |                      | I <sub>D</sub>                    | -4.7         | А    |  |
| Pulsed Drain Current, V <sub>GS</sub> @ 4.5V            |                      | I <sub>DM</sub>                   | -20          | А    |  |
| Continuous Source Current (Diode Conduction) (Note 1,2) |                      | I <sub>S</sub>                    | -2.5         | А    |  |
| Maximum Power Dissipation                               | T <sub>A</sub> =25°C | P <sub>D</sub>                    | 2            | W    |  |
|   | T <sub>A</sub> =70°C |                                   | 1.3          |      |  |
| Operating Junction Temperature                          |                      | TJ                                | +150         | °C   |  |
| Operating Junction and Storage Temperature Range        |                      | T <sub>J</sub> , T <sub>STG</sub> | - 55 to +150 | °C   |  |

#### Thermal Performance

| Thermal Lenormance                                   |                  |       |      |  |  |
|--|------------------|-------|------|--|--|
| Parameter  | Symbol           | Limit | Unit |  |  |
| Junction to Case Thermal Resistance                  | R <sub>eJC</sub> | 30    | °C/W |  |  |
| Junction to Ambient Thermal Resistance (PCB mounted) | R <sub>OJA</sub> | 62.5  | °C/W |  |  |



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**Electrical Specifications** (T<sub>J</sub>=25°C unless otherwise noted)

| Parameter                        | Conditions   | Symbol              | Min  | Тур  | Max  | Unit |
|----------------------------------|--|---------------------|------|------|------|------|
| Static (Note 3)                  |  |                     |      |      |      |      |
| Drain-Source Breakdown Voltage   | $V_{GS} = 0V, I_D = -250\mu A$   | BV <sub>DSS</sub>   | -20  |      |      | V    |
| Gate Threshold Voltage           | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$  | V <sub>GS(TH)</sub> | -0.6 |      | -1.4 | V    |
| Gate Body Leakage                | $V_{GS} = \pm 12V, V_{DS} = 0V$  | I <sub>GSS</sub>    |      |      | ±100 | nA   |
| Zero Gate Voltage Drain Current  | $V_{DS} = -20V, V_{GS} = 0V$   | I <sub>DSS</sub>    |      |      | -1.0 | μA   |
| On-State Drain Current           | $V_{DS} = -5V, V_{GS} = -4.5V$   | I <sub>D(ON)</sub>  | -15  |      |      | Α    |
| Drain-Source On-State Resistance | $V_{GS} = -4.5V, I_D = -4.7A$  |                     |      | 48   | 60   | mΩ   |
|                                  | $V_{GS} = -4.5V, I_D = -2.9A$  |                     |      | 47   | 58   |      |
|                                  | $V_{GS} = -2.7V, I_{D} = -1.5A$  | R <sub>DS(ON)</sub> |      | 60   | 78   |      |
|                                  | $V_{GS} = -2.5V, I_D = -3.8A$  | ]                   |      | 65   | 85   |      |
| Forward Transconductance         | $V_{DS} = -10V, I_{D} = -4.7A$   | 9 <sub>fs</sub>     |      | 11   |      | S    |
| Diode Forward Voltage            | $I_S = -1.7A$ , $V_{GS} = 0V$  | $V_{SD}$            |      | -0.8 | -1.2 | V    |
| Dynamic (Note 4,5)               |  |                     |      |      |      |      |
| Total Gate Charge                | ., ,,,,  | Qg                  |      | 6    | 9    |      |
| Gate-Source Charge               | $V_{DS} = -10V, I_{D} = -4.7A,$  | $Q_{gs}$            |      | 1.4  |      | nC   |
| Gate-Drain Charge                | $V_{GS} = -4.5V$   | $Q_{gd}$            |      | 1.9  |      |      |
| Input Capacitance                |  | C <sub>iss</sub>    |      | 640  |      |      |
| Output Capacitance               | $V_{DS} = -10V, V_{GS} = 0V,$<br>f = 1.0MHz                                    | C <sub>oss</sub>    |      | 180  |      | pF   |
| Reverse Transfer Capacitance     |  | C <sub>rss</sub>    |      | 90   |      |      |
| Switching (Note 4,5)             |  |                     |      |      |      |      |
| Turn-On Delay Time               | $V_{DD} = -10V, R_L = 10\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$ | t <sub>d(on)</sub>  |      | 22   | 35   |      |
| Turn-On Rise Time                |  | t <sub>r</sub>      |      | 35   | 55   |      |
| Turn-Off Delay Time              |  | t <sub>d(off)</sub> |      | 45   | 70   | ns   |
| Turn-Off Fall Time               |  | t <sub>f</sub>      |      | 25   | 50   |      |

#### Notes:

- 1. Pulse width limited by the Maximum junction temperature
- 2. Surface Mounted on FR4 Board, t ≤ 5 sec.
- 3. pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

Version: E15

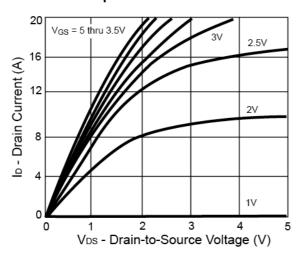


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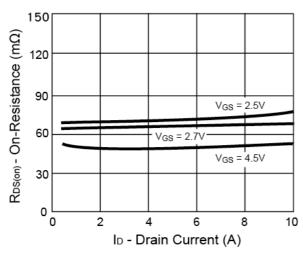


#### **Electrical Characteristics Curves**

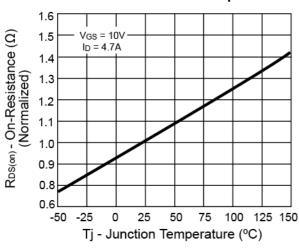
#### **Output Characteristics**



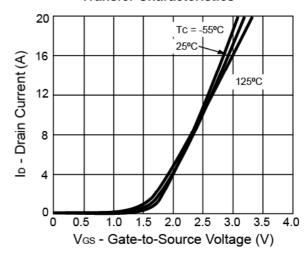
#### **On-Resistance vs. Drain Current**



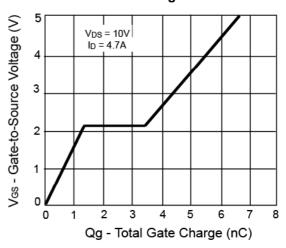
**On-Resistance vs. Junction Temperature** 



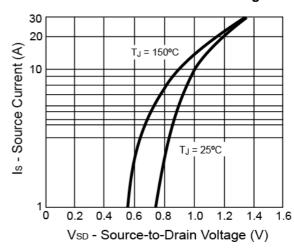
**Transfer Characteristics** 



**Gate Charge** 



Source-Drain Diode Forward Voltage



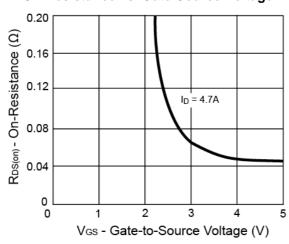


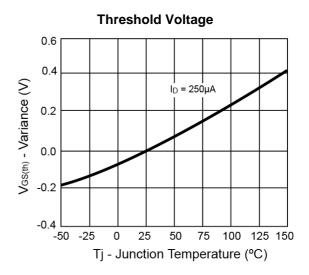
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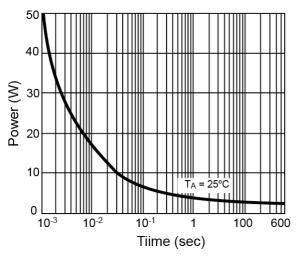
#### **Electrical Characteristics Curves**

#### On-Resistance vs. Gate-Source Voltage

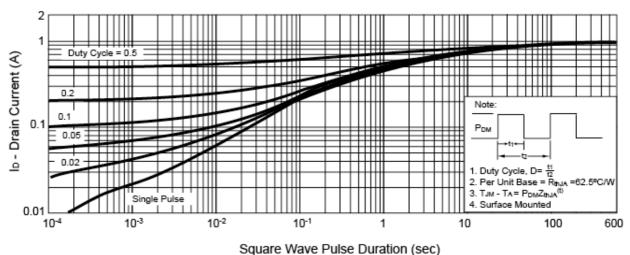




#### **Single Pulse Power**



### Normalized Thermal Transient Impedance, Junction-to-Ambient

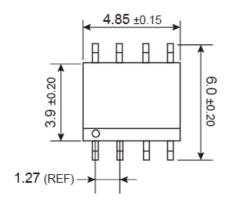


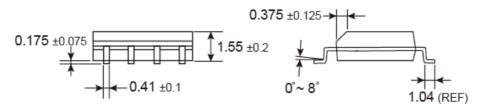


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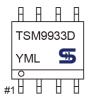
## **SOP-8 Mechanical Drawing**





Unit: Millimeters

## **Marking Diagram**



Y = Year Code

**M** = Month Code for Halogen Free Product

 $oldsymbol{O}$  =Jan  $oldsymbol{P}$  =Feb  $oldsymbol{Q}$  =Mar  $oldsymbol{R}$  =Apr

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$ 

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W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



# TSM9933DCS -20V P-Channel Power MOSFET



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